Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

July 2016

FDMC2610
N-Channel UltraFET Trench® MOSFET
200V, 9.5A, 200mΩ

Features

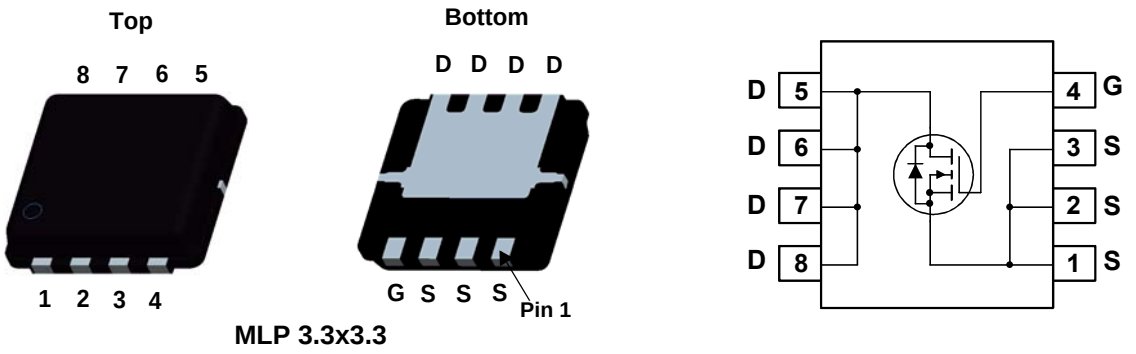
- Max $r_{DS(on)}$ = 200mΩ at V_{GS} = 10V, I_D = 2.2A
- Max $r_{DS(on)}$ = 215mΩ at V_{GS} = 6V, I_D = 1.5A
- Low Profile - 1mm Max in a Power 33
- RoHS Compliant

General Description

This N-Channel MOSFET is a rugged gate version of Fairchild Semiconductor's advanced Power Trench process. It has been optimized for power management applications.

Application

- DC - DC Conversion



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted.

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			200	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous (Silicon limited)	T_C = 25°C		9.5	A
	-Continuous	T_A = 25°C	(Note 1a)	2.2	
	-Pulsed			15	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	6	mJ
P_D	Power Dissipation	T_C = 25°C		42	W
	Power Dissipation	T_A = 25°C	(Note 1a)	2.1	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	60	

Package Marking and Ordering Information

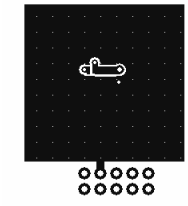
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC2610	FDMC2610	MLP 3.3x3.3	13 ”	12 mm	3000 units

Electrical Characteristics T_J = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	200			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		199		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 160V, V_{GS} = 0V			1	μA
		V_{DS} = 160V, V_{GS} = 0V, T_J = 125°C			100	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	2	3.2	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		-9.9		mV/°C
$r_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 10V, I_D = 2.2A		175	200	mΩ
		V_{GS} = 6V, I_D = 1.5A		188	215	mΩ
		V_{GS} = 10V, I_D = 2.2A , T_J = 125°C		347	397	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 5V, I_D = 2.2A		7		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 100V, V_{GS} = 0V, f = 1MHz		720	960	pF
C_{oss}	Output Capacitance			41	55	pF
C_{rss}	Reverse Transfer Capacitance			12	20	pF
R_g	Gate Resistance	f = 1MHz		0.7		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 100V, I_D = 2.2A, V_{GS} = 10V, R_{GEN} = 24Ω		17	31	ns
t_r	Rise Time			13	24	ns
$t_{d(off)}$	Turn-Off Delay Time			29	47	ns
t_f	Fall Time			16	29	ns
$Q_{g(TOT)}$	Total Gate Charge at 10V	V_{GS} = 0V to 10V, V_{DD} = 100V, I_D = 2.2A		12.3	18	nC
Q_{gs}	Gate to Source Gate Charge			3		nC
Q_{gd}	Gate to Drain “Miller” Charge			3.6		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = 2.2A (Note 2)		0.8	1.2	V
t_{rr}	Reverse Recovery Time	I_F = 2.2A, di/dt = 100A/μs		69	104	ns
Q_{rr}	Reverse Recovery Charge			114	171	nC

Notes:

1: $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 60°C/W when mounted on a 1 in^2 pad of 2 oz copper

b. 135°C/W when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.

3. Starting T_J = 25 °C; N-ch: L = 3 mH, I_{AS} = 2 A, V_{DD} = 200 V, V_{GS} = 10 V.

Typical Characteristics T_J = 25°C unless otherwise noted.

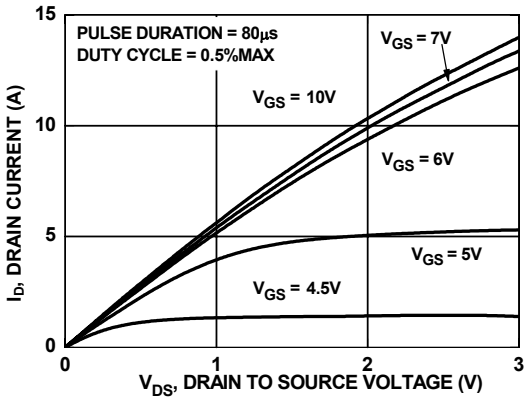


Figure 1. On-Region Characteristics

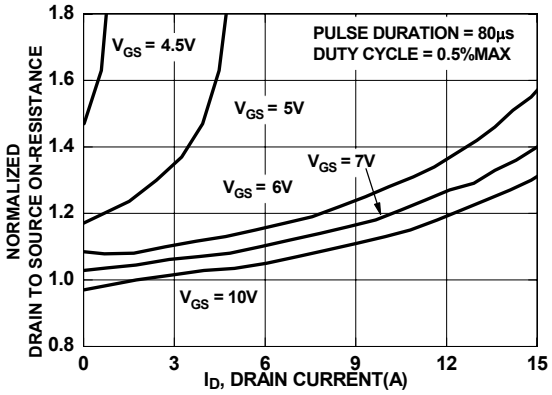


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

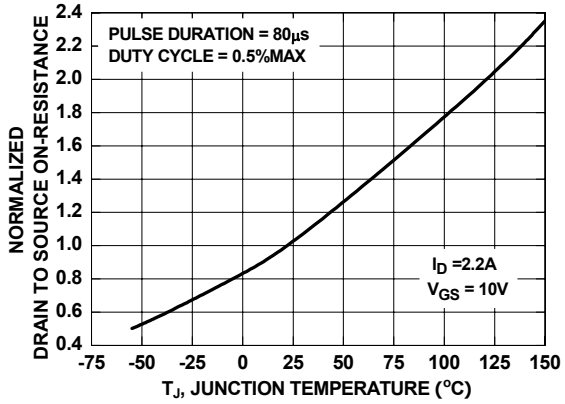


Figure 3. Normalized On-Resistance vs Junction Temperature

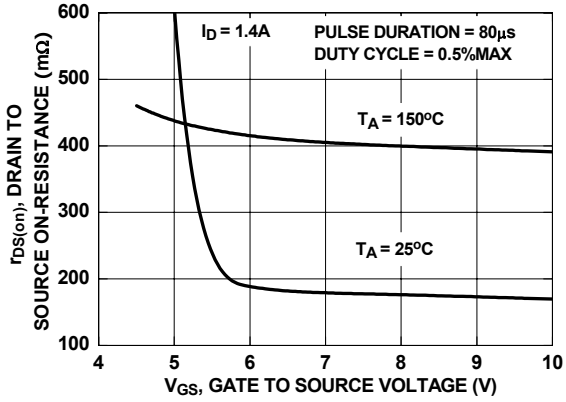


Figure 4. On-Resistance vs Gate to Source Voltage

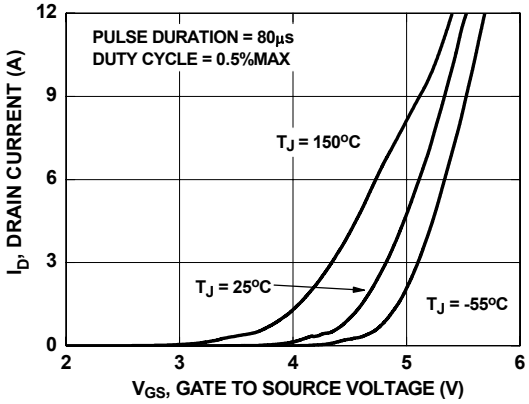


Figure 5. Transfer Characteristics

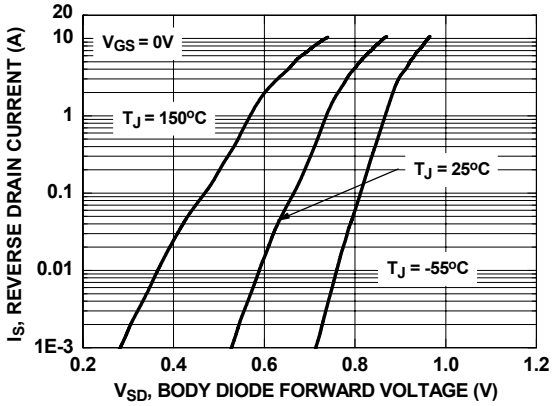


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted.

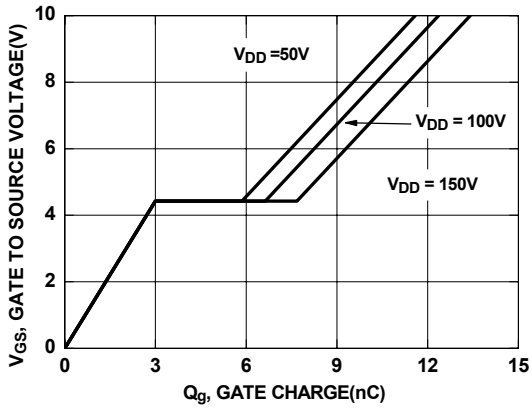


Figure 7. Gate Charge Characteristics

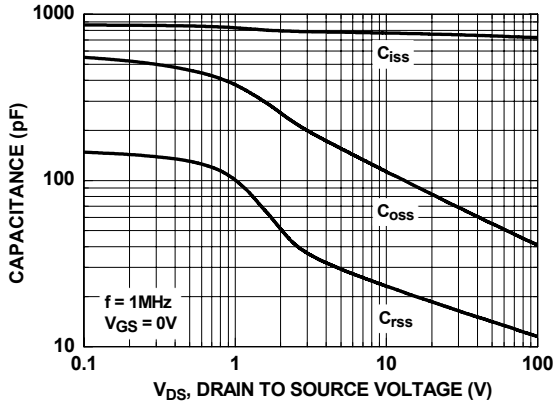


Figure 8. Capacitance vs Drain to Source Voltage

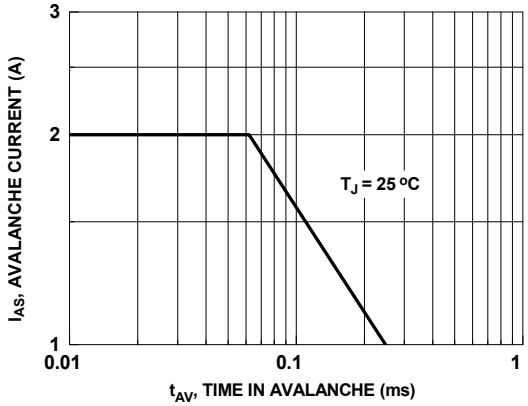


Figure 9. Unclamped Inductive Switching Capability

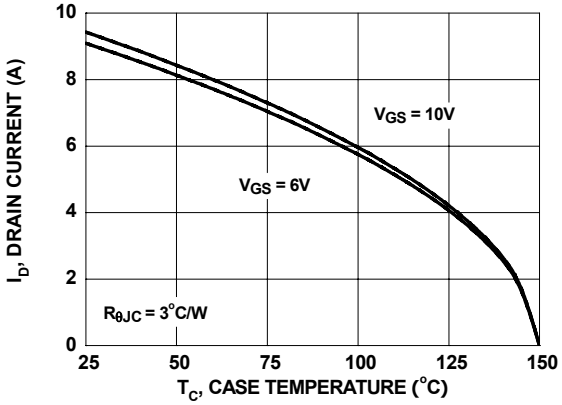


Figure 10. Maximum Continuous Drain Current vs Case Temperature

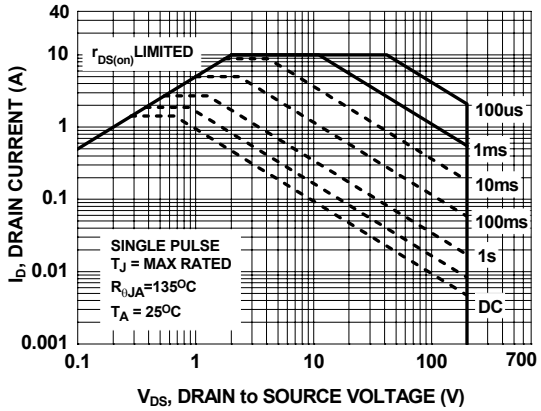


Figure 11. Forward Bias Safe Operating Area

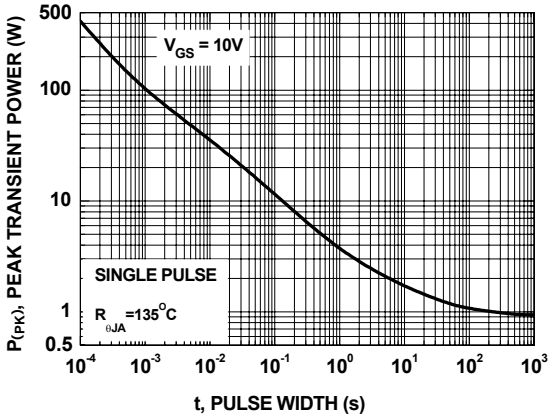


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted.

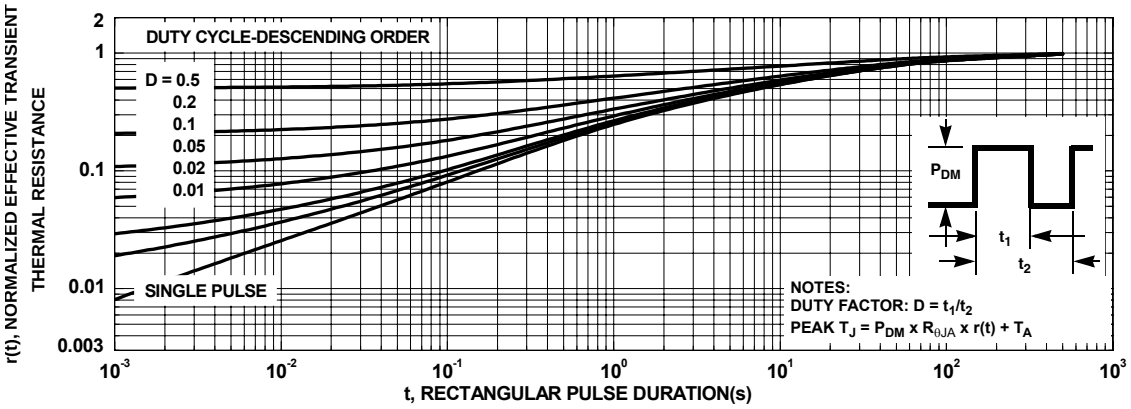
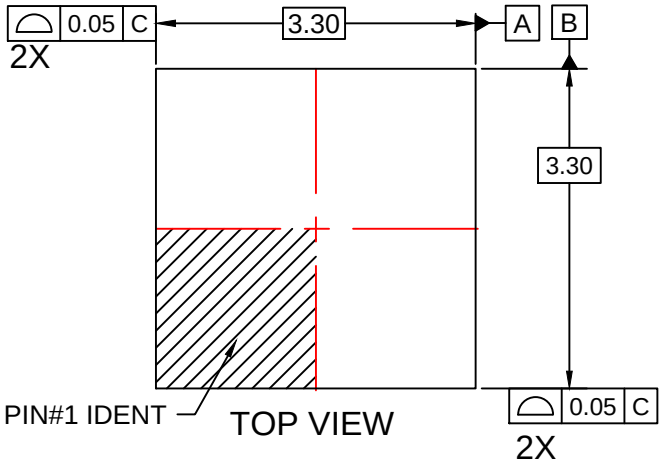
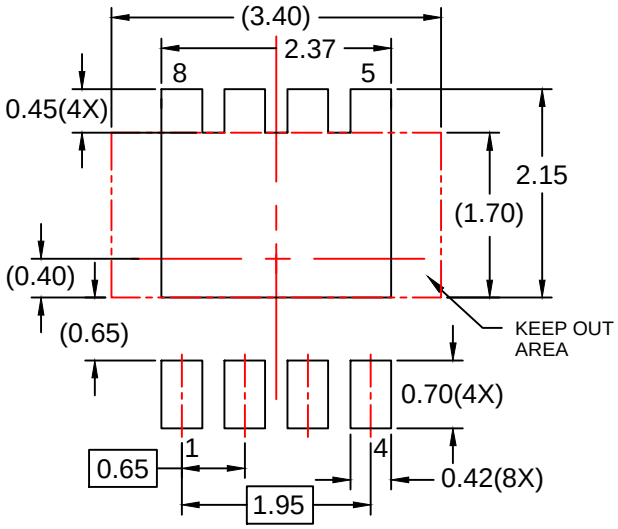
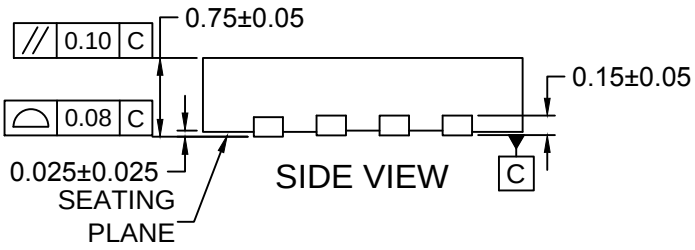


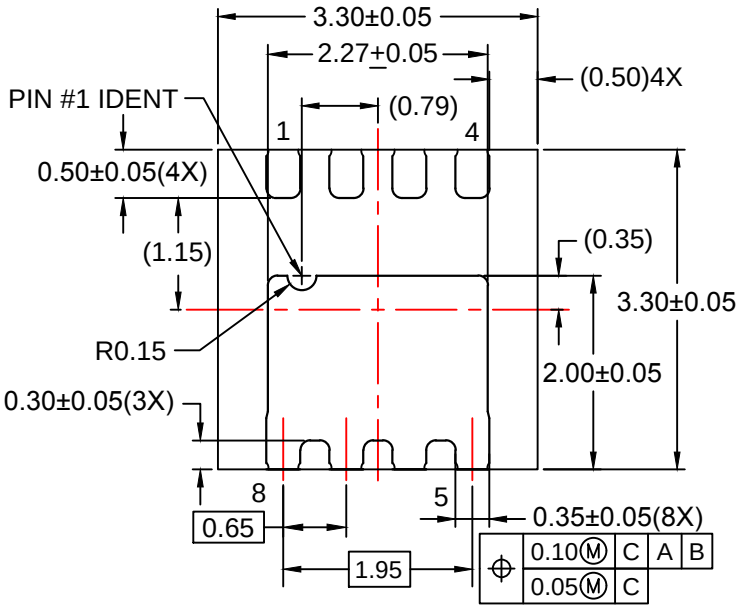
Figure 13. Transient Thermal Response Curve





RECOMMENDED LAND PATTERN





BOTTOM VIEW

NOTES:

A. DOES NOT CONFORM TO JEDEC REGISTRATION MO-229

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

E. DRAWING FILENAME: MKT-MLP08Srev3.

FAIRCHILD

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by ON Semiconductor ***manufacturer:***

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B